

## ABSTRACT

A semiconductor integrated circuit is provided, which has an improved withstanding voltage for electrostatic breakdown at the time of electrostatic discharge by the charged device model, in the case of protecting a MOS capacitor provided at the input side of the internal circuit. The semiconductor integrated circuit comprises an internal circuit 20 for inputting an external signal, an internal circuit MOS capacitor 16, one end of which is connected to a power source wire 10 for supplying the source voltage and the other end of which is connected to a ground potential wire 12 for supplying the ground potential; a ground terminal 14 to which one end of the ground potential wire is connected; an electrostatic protection element 18 connected in parallel with the MOS capacitor 16 between the ground terminal 14 and the MOS capacitor, wherein the MOS capacitor and the electrostatic protection element are connected between the power source wire and the ground potential wire such that the wire resistance R1 of the ground potential wire between the ground terminal and the connection point with one end of the electrostatic protection element is larger than the wire resistance R2 of the ground potential wire between the connection point with one end of the electrostatic protection element and the connection point with one end of the MOS capacitor.